

N-channel 40 V 1.6 mΩ standard level MOSFET in TO220 15 July 2013 Product data sheet

## 1. General description

Standard level N-channel MOSFET in SOT78 (TO220) using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

## 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Robust construction for demanding applications
- Standard level gate

## 3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

## 4. Quick reference data

Table 1. C	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	150	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	338	W
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13		-	1.9	2.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 14	[2]	-	1.3	1.6	mΩ
Dynamic cl	naracteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 75 A; V <sub>DS</sub> = 20 V;		-	32	-	nC
Q <sub>G(tot)</sub>	total gate charge	T <sub>j</sub> = 25 °C; <u>Fig. 15; Fig. 16</u>		-	136	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 150 A; $V_{sup}$ ≤ 40 V; unclamped; $R_{GS}$ = 50 Ω; $t_p$ = 0.1 ms; Fig. 3		-	-	1.1	J

Continuous current is limited by package Measured 3 mm from package. [1]

[2]

#### **Pinning information** 5.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	204	
3	S	source		G-UT4
mb	D	drain	TO-220AB (SOT78)	mbb076 S

#### **Ordering information** 6.

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN1R5-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

#### Marking 7.

Fable 4. Marking codes	
Type number	Marking code
PSMN1R5-40PS	PSMN1R5-40PS

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## 8. Limiting values

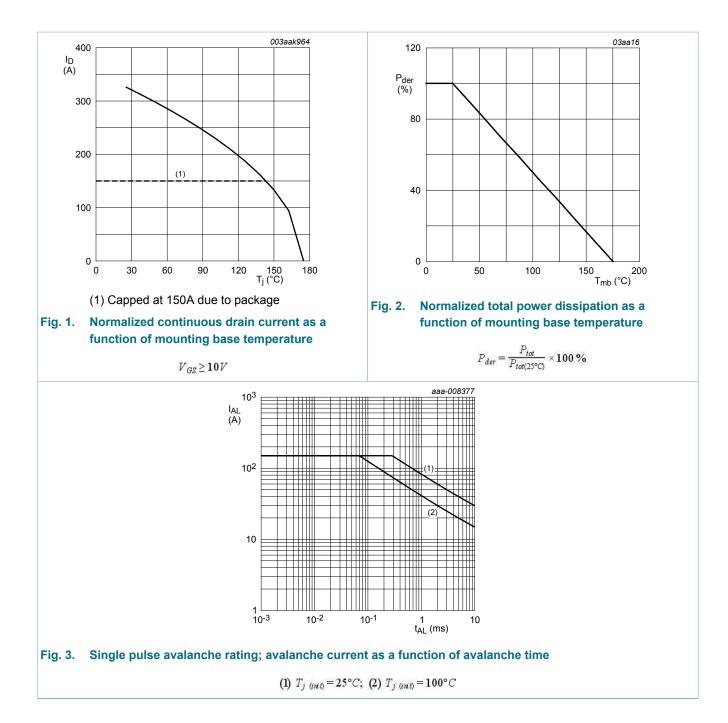
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	150	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	150	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 4		-	1301	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	338	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	150	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	1301	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; \text{V}; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \text{I}_{D} = 150 \; \text{A}; \\ V_{sup} \leq 40 \; \text{V}; \; \text{unclamped}; \; \text{R}_{GS} = 50 \; \Omega; \\ t_{p} = 0.1 \; \text{ms}; \; \underline{\text{Fig. 3}} \end{array} $		-	1.1	J

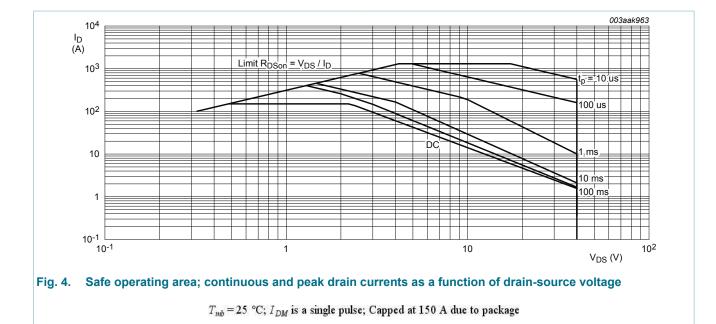
[1] Continuous current is limited by package

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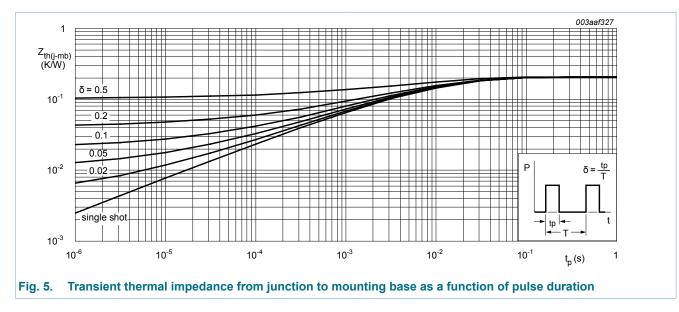
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## 9. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.22	0.44	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



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## **10. Characteristics**

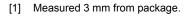
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics						
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C		36	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 11		-	-	4.6	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 11		1	-	-	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 25 \text{ °C;}$ Fig. 12; Fig. 11		2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	0.02	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C		-	250	500	μA
I <sub>GSS</sub> g	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 13		-	1.9	2.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 13		-	2.6	3.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 14	[1]	-	1.3	1.6	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz		-	1.1	-	Ω
Dynamic ch	aracteristics						
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 0 A; $V_{DS}$ = 0 V; $V_{GS}$ = 10 V		-	133	-	nC
		$I_D$ = 75 A; $V_{DS}$ = 20 V; $V_{GS}$ = 10 V;		-	136	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	52	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge			-	30	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			-	22.5	-	nC
Q <sub>GD</sub>	gate-drain charge			-	32	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 75 A; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C; <u>Fig. 15; Fig. 16</u>		-	6.1	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	9710	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 17</u>		-	2042	-	pF

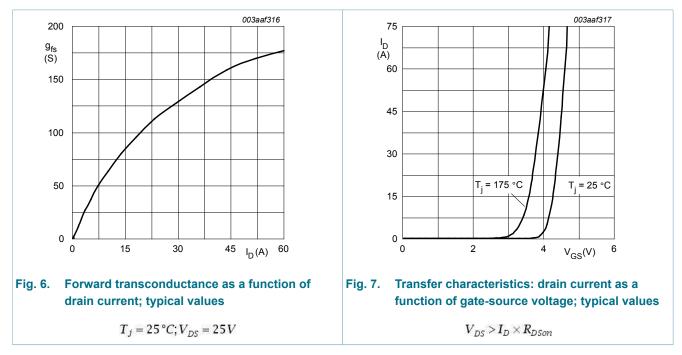
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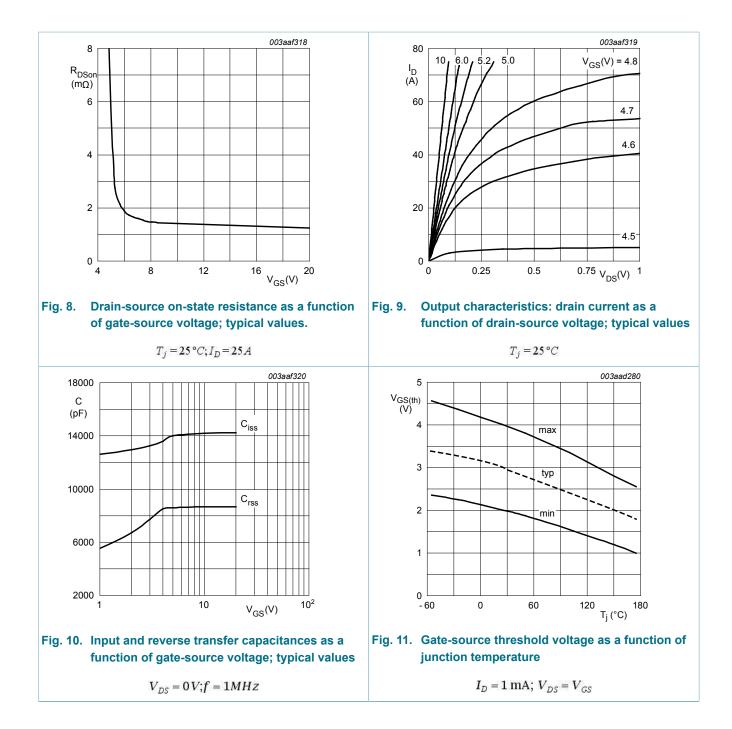
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>rss</sub>	reverse transfer capacitance		-	994	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; R <sub>L</sub> = 0.8 Ω; V <sub>GS</sub> = 10 V;	-	45	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 4.7 Ω; T <sub>j</sub> = 25 °C	-	66	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	111	-	ns
t <sub>f</sub>	fall time	-	-	53	-	ns
Source-drain	n diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 18</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}$	-	64	-	ns
Q <sub>r</sub>	recovered charge	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	117	-	nC





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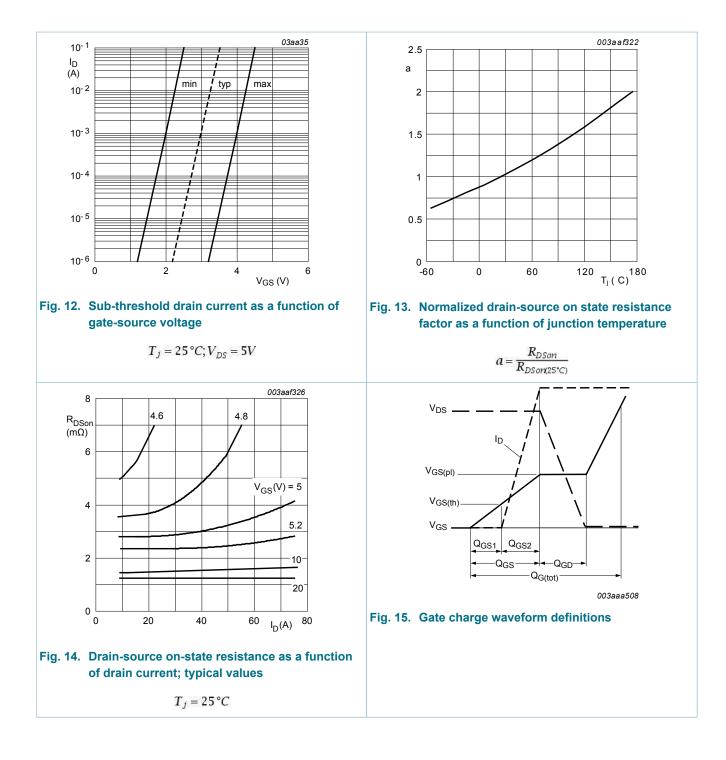
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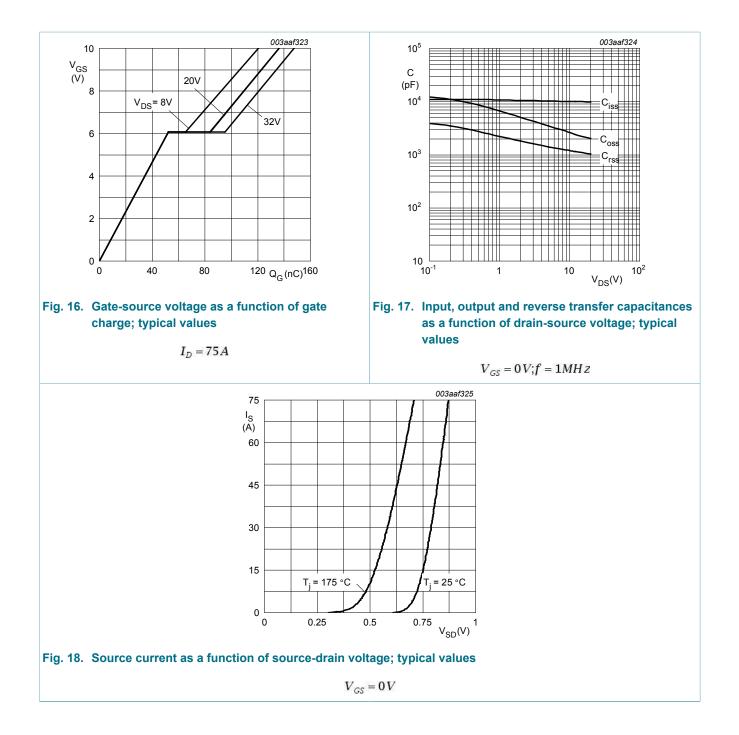
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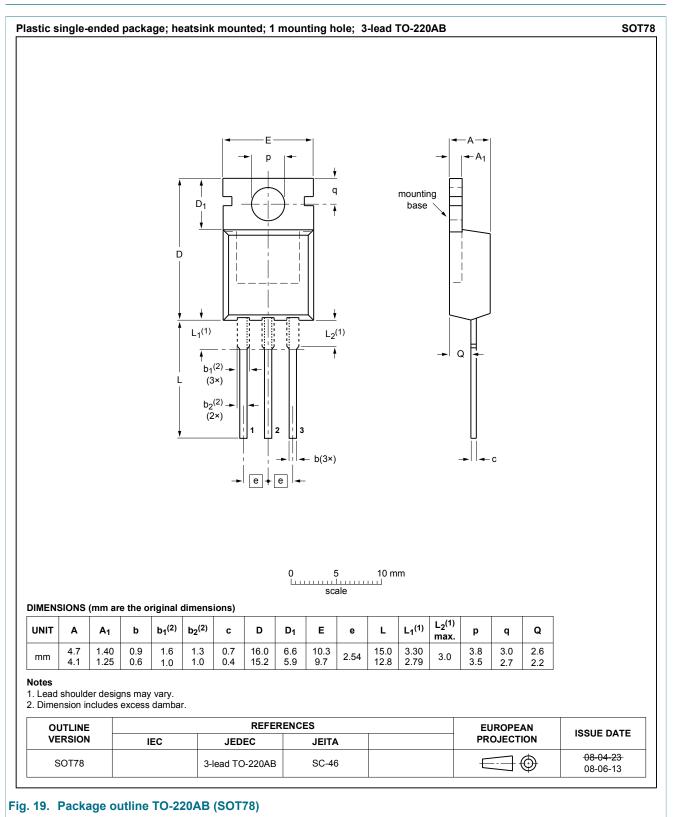
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## 11. Package outline



#### PSMN1R5-40PS

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